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WHAT IS CLAIMED IS:

1. A semiconductor laser device comprising:  
a heat radiating block;  
one or more first semiconductor laser element(s)  
5 arranged on said heat radiating block in a manner where one  
electrode is in contact therewith; and  
one or more second semiconductor laser element(s)  
arranged on said heat radiating block in an electrically  
insulated manner via a dielectric layer.
- 10 2. The semiconductor laser device as set forth in  
Claim 1, wherein  
said first and second semiconductor laser elements are  
both integrated into one chip, and one electrode of the  
first semiconductor laser element is in contact with said  
15 block, and the second semiconductor laser element is  
provided on said dielectric layer.
3. The semiconductor laser device as set forth in  
Claim 1, wherein  
said heat radiating block is an electrical conductor  
20 or a semiconductor.
4. The semiconductor laser device as set forth in  
Claim 2, wherein  
said heat radiating block is an electrical conductor  
or a semiconductor.
- 25 5. The semiconductor laser device as set forth in  
Claim 1, comprising:  
a light output monitoring photodiode built onto said  
heat radiating block.

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6. The semiconductor laser device as set forth in  
Claim 2, comprising:

a light output monitoring photodiode built onto said  
heat radiating block.

5        7. The semiconductor laser device as set forth in  
Claim 3, comprising:

a light output monitoring photodiode built onto said  
heat radiating block.

8. The semiconductor laser device as set forth in  
10 Claim 1, wherein

said dielectric layer is formed of one selected from a  
group consisting of silicon oxide, silicon nitride, titanium  
oxide, aluminum oxide, and aluminum nitride.

9. The semiconductor laser device as set forth in  
15 Claim 2, wherein

said dielectric layer is formed of one selected from a  
group consisting of silicon oxide, silicon nitride, titanium  
oxide, aluminum oxide, and aluminum nitride.

10. The semiconductor laser device as set forth in  
20 Claim 3, wherein

said dielectric layer is formed of one selected from a  
group consisting of silicon oxide, silicon nitride, titanium  
oxide, aluminum oxide, and aluminum nitride.

11. The semiconductor laser device as set forth in  
25 Claim 1, wherein

said first semiconductor laser element is greater in  
heat generation during driving or smaller in heat radiation  
from an element exposed surface than said second

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semiconductor laser element.

12. The semiconductor laser device as set forth in  
Claim 2, wherein

5 said first semiconductor laser element is greater in  
heat generation during driving or smaller in heat radiation  
from an element exposed surface than said second  
semiconductor laser element.

13. The semiconductor laser device as set forth in  
Claim 3, wherein

10 said first semiconductor laser element is greater in  
heat generation during driving or smaller in heat radiation  
from an element exposed surface than said second  
semiconductor laser element.

14. The semiconductor laser device as set forth in  
15 Claim 1, wherein

said first semiconductor laser element is a  
semiconductor laser to emit a laser beam with a 650nm-band  
wavelength, and said second semiconductor laser element is a  
semiconductor laser to emit a laser beam with a 780nm-band  
20 wavelength.

15. The semiconductor laser device as set forth in  
Claim 2, wherein

said first semiconductor laser element is a  
semiconductor laser to emit a laser beam with a 650nm-band  
25 wavelength, and said second semiconductor laser element is a  
semiconductor laser to emit a laser beam with a 780nm-band  
wavelength.

16. The semiconductor laser device as set forth in

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Claim 3, wherein

said first semiconductor laser element is a  
semiconductor laser to emit a laser beam with a 650nm-band  
wavelength, and said second semiconductor laser element is a  
5 semiconductor laser to emit a laser beam with a 780nm-band  
wavelength.